

FIG. 1

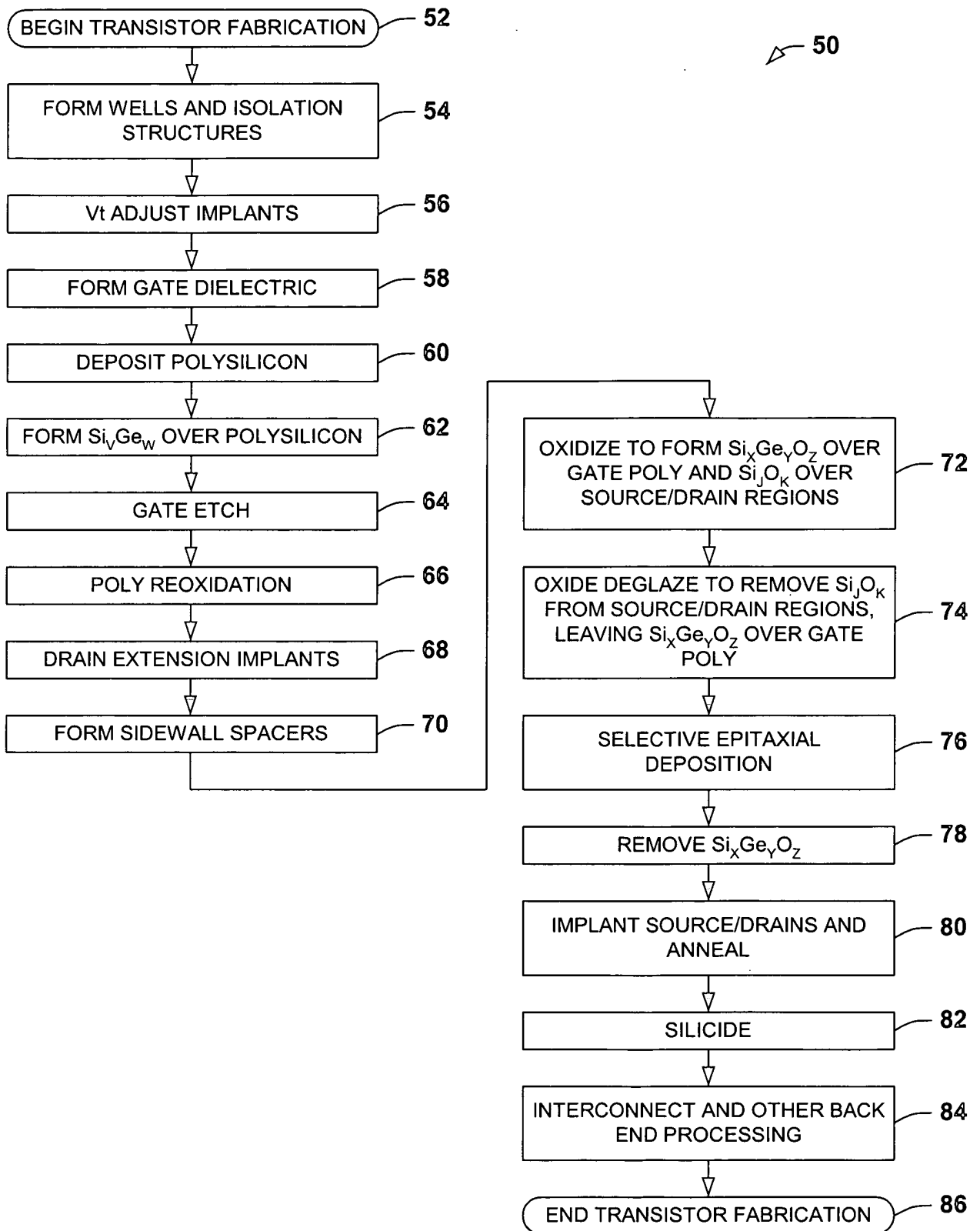


FIG. 2

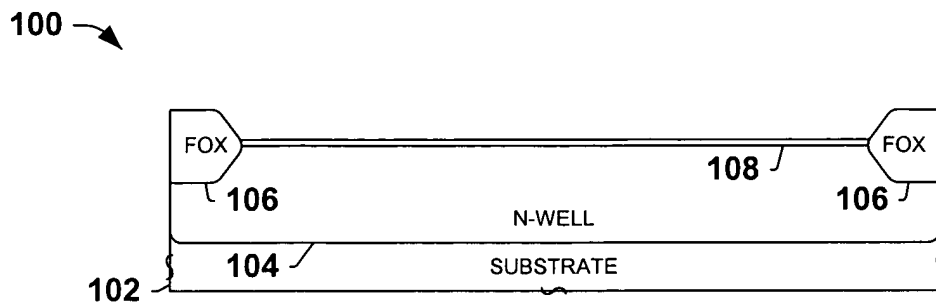


FIG. 3A

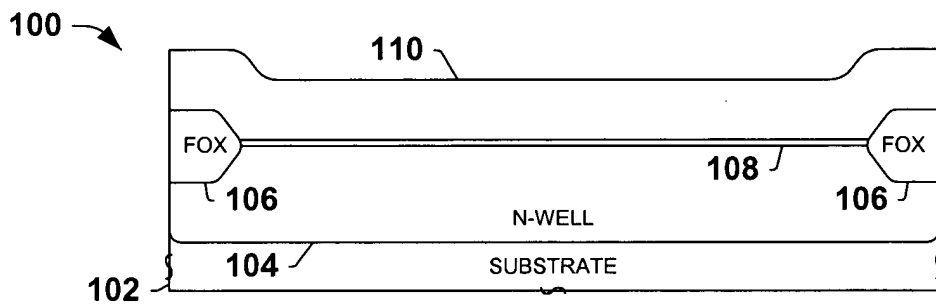


FIG. 3B

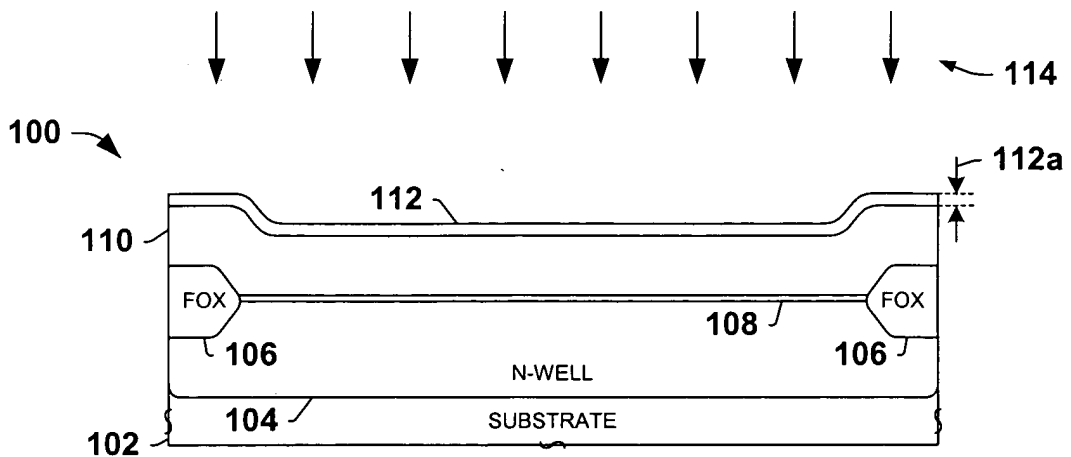


FIG. 3C

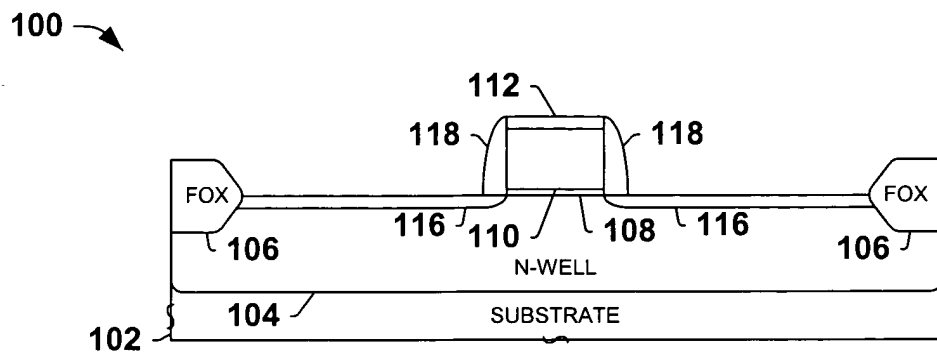


FIG. 3D

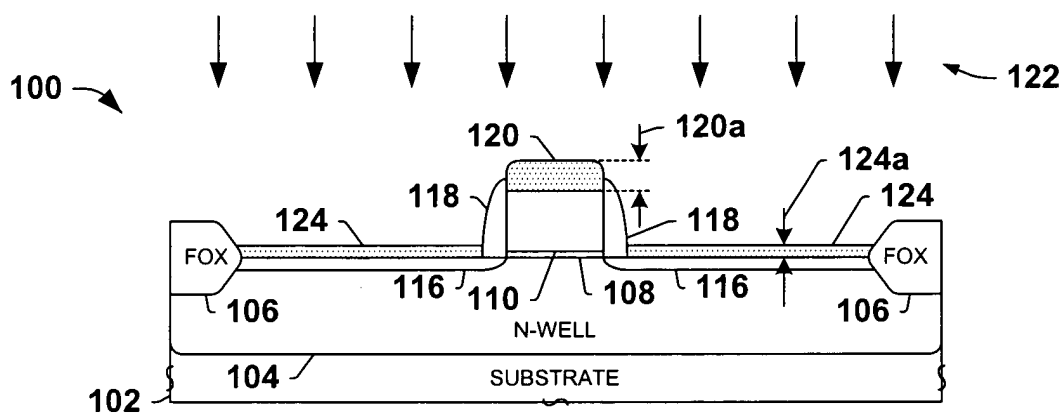


FIG. 3E

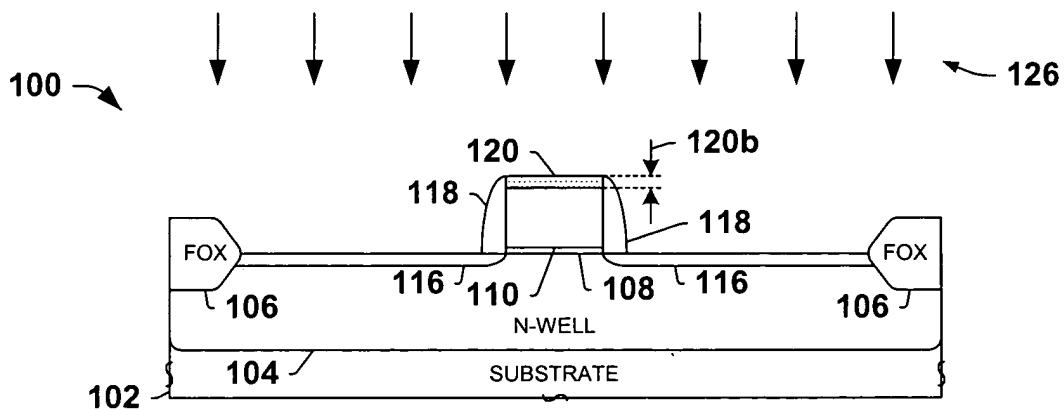


FIG. 3F

A cross-sectional view of a semiconductor device 100. The device is built on a substrate 102, which includes an N-WELL region 104. A layer 106 is formed on the substrate, containing regions labeled FOX. A layer 130 is formed on top of layer 106, with regions 116 and 118. A central region 110 is defined by two vertical structures 108. Arrows 134 indicate light incident on the top surface of the device.

100

138

140

118

136

FOX

106

116

110

N-WELL

108

116

106

102

104

SUBSTRATE

FIG. 31

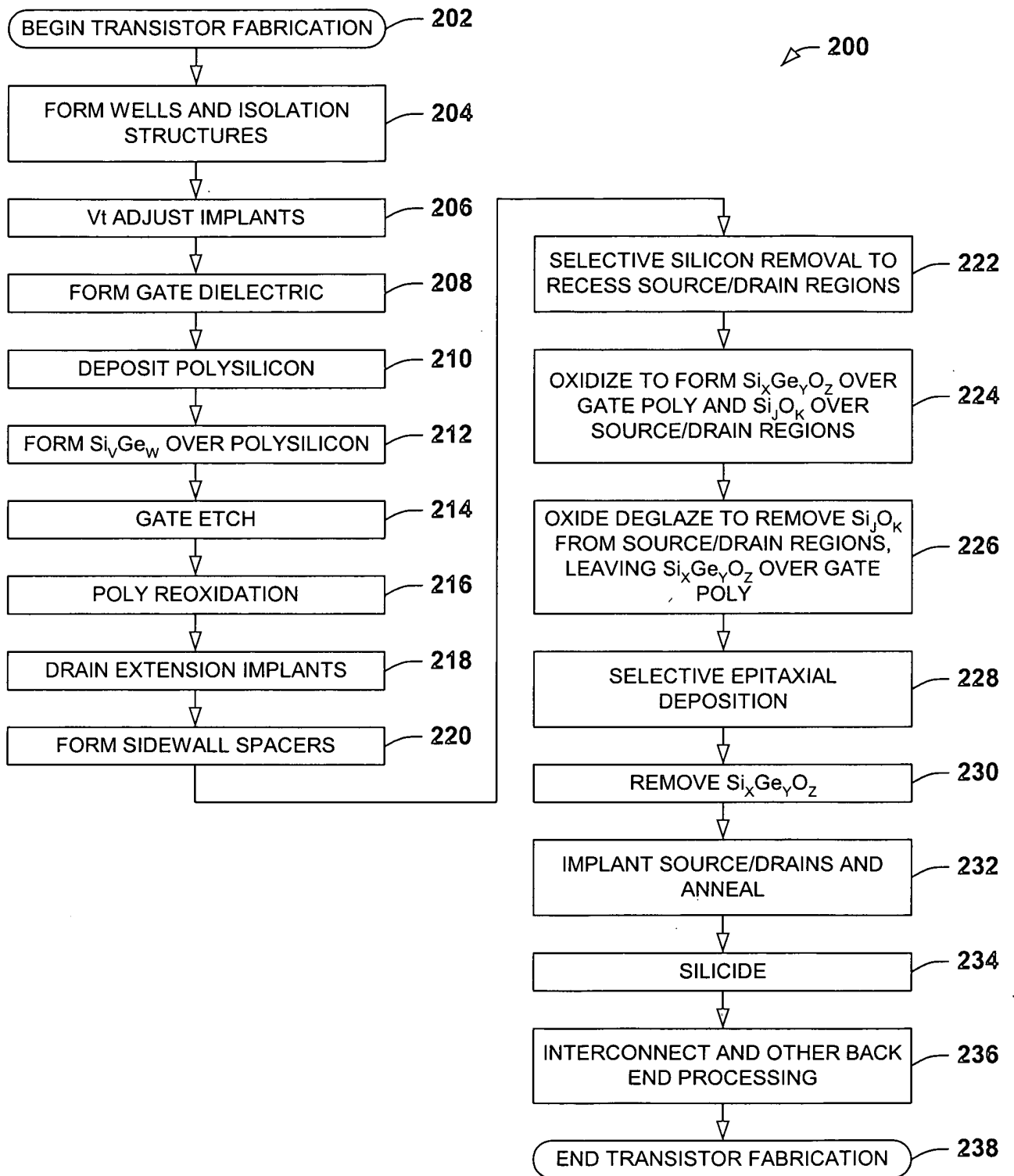


FIG. 4

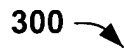


FIG. 5A

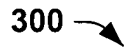


FIG. 5B

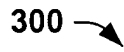


FIG. 5C

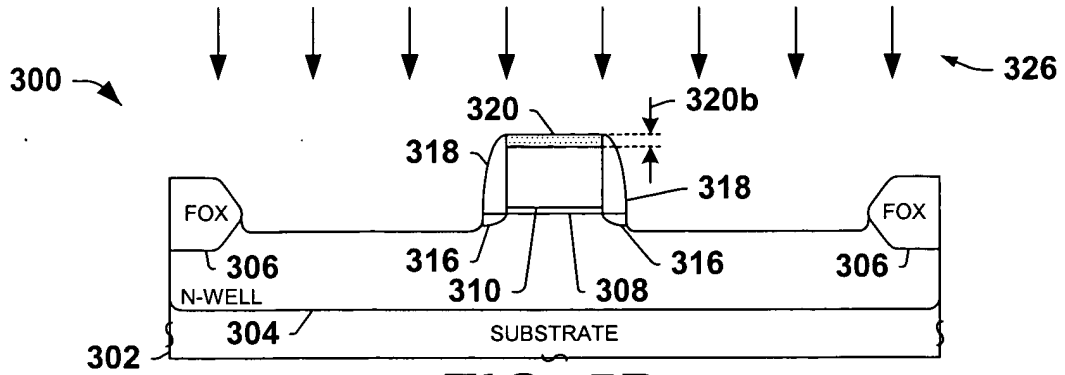


FIG. 5D

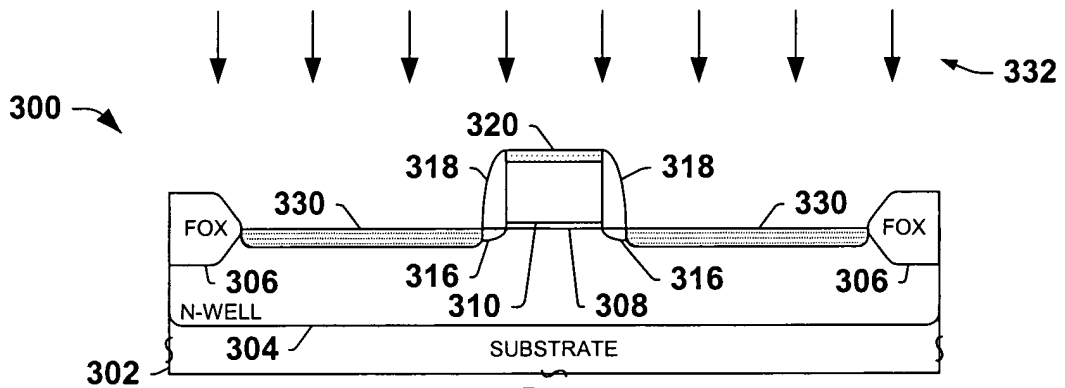


FIG. 5E

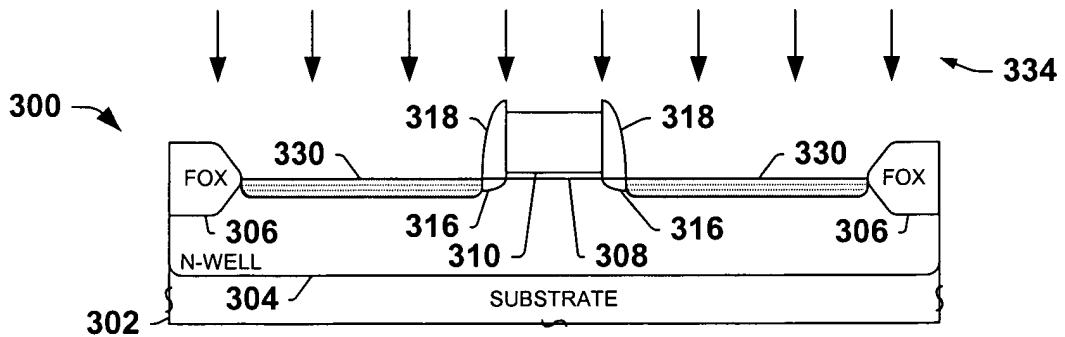


FIG. 5F

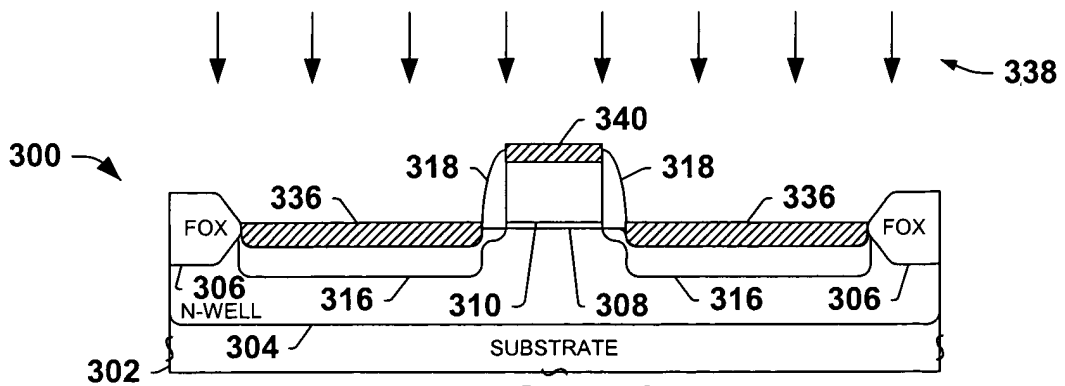


FIG. 5G

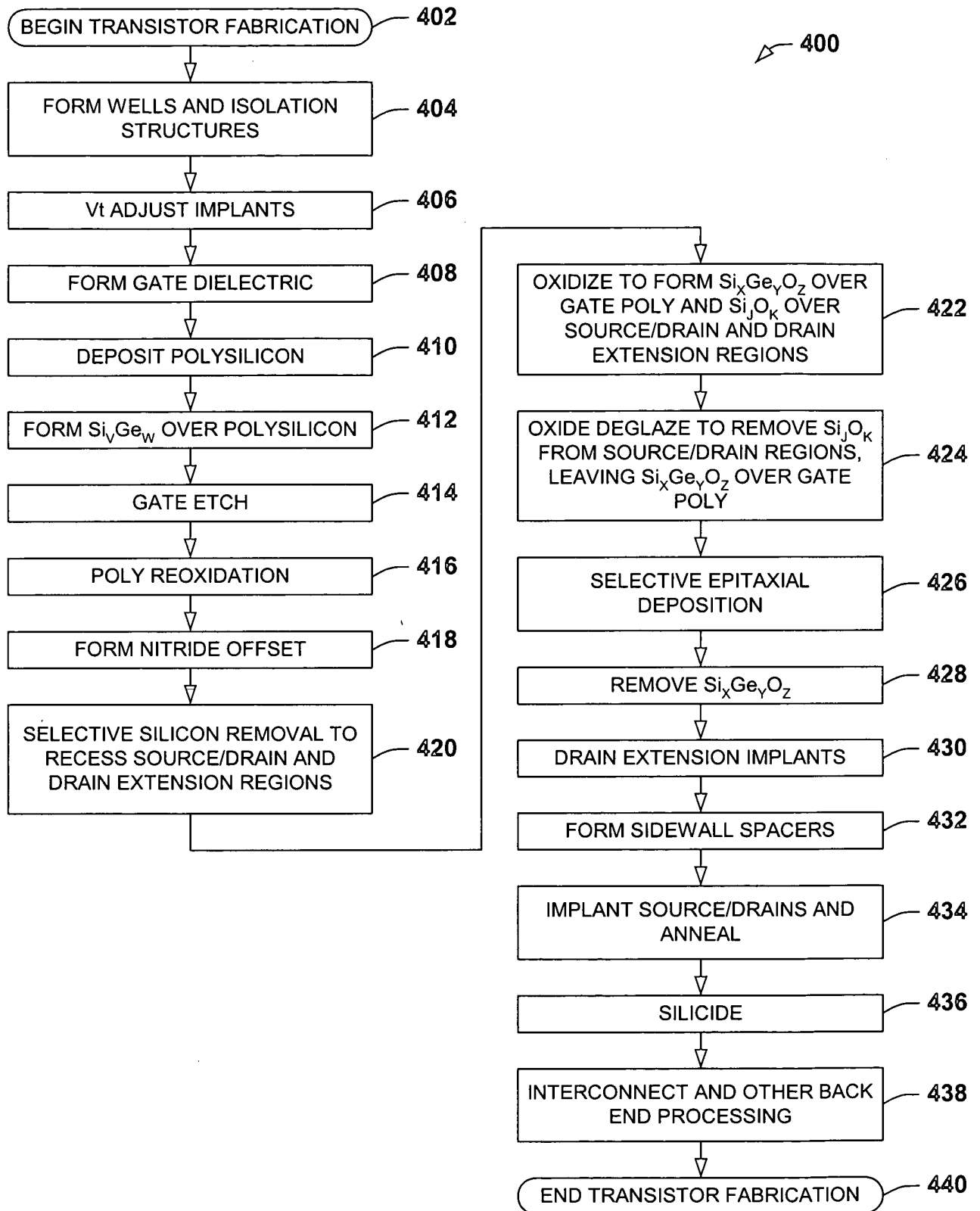


FIG. 6

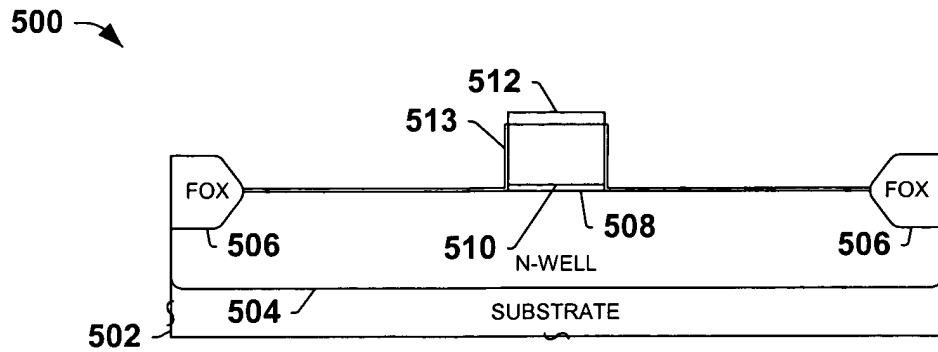


FIG. 7A

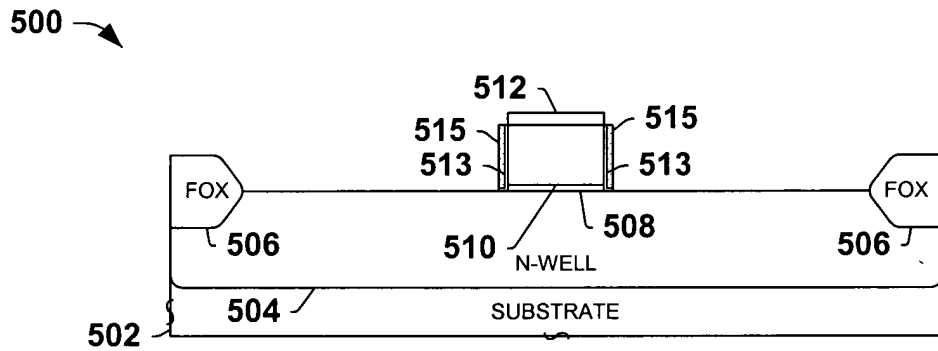


FIG. 7B

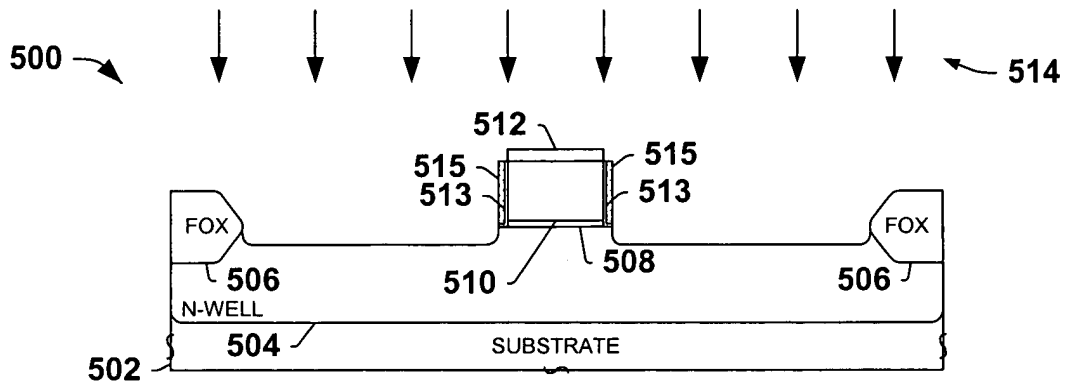


FIG. 7C

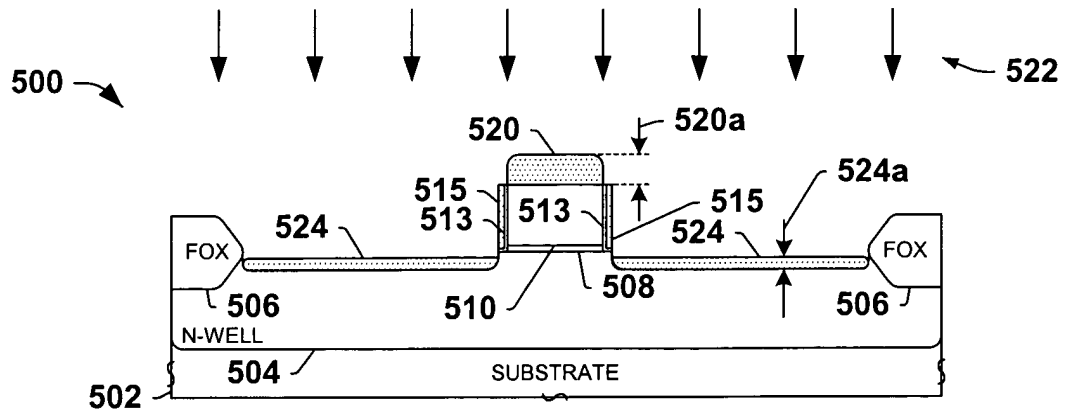


FIG. 7D

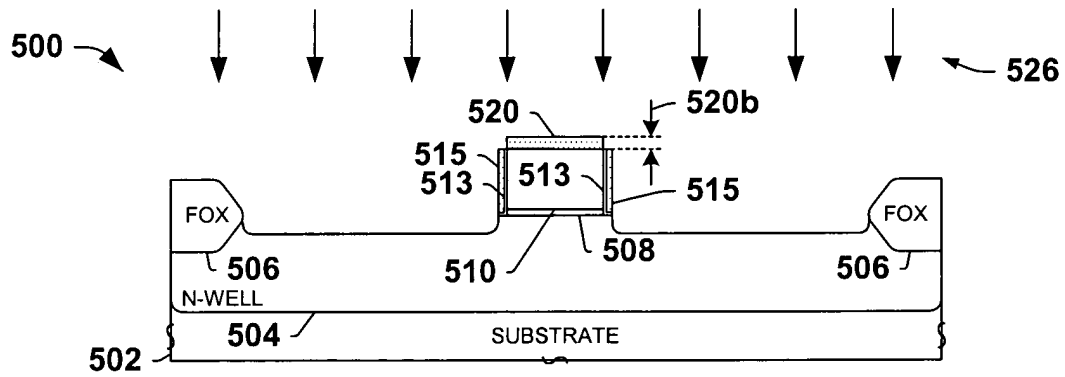


FIG. 7E

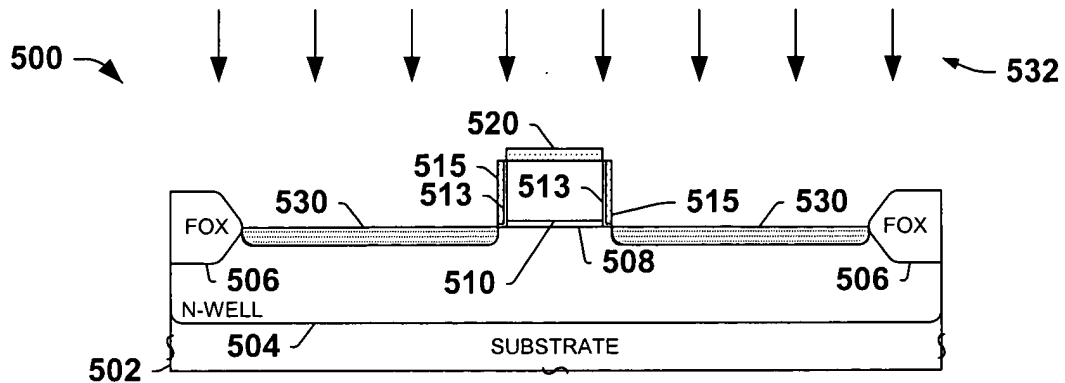


FIG. 7F

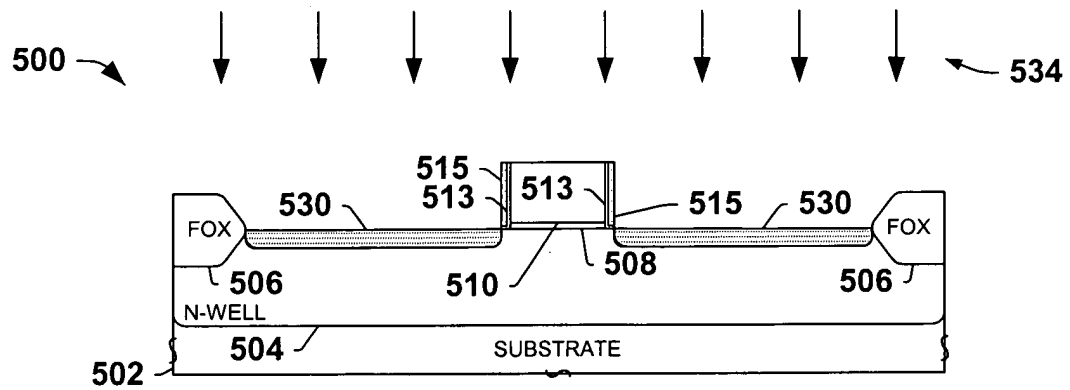


FIG. 7G

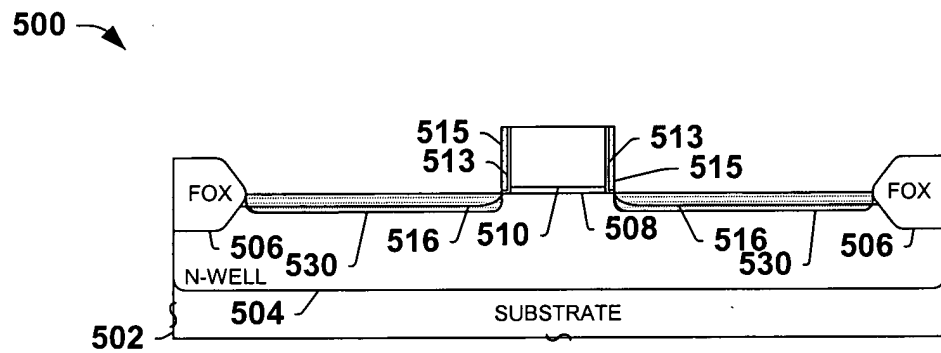


FIG. 7H

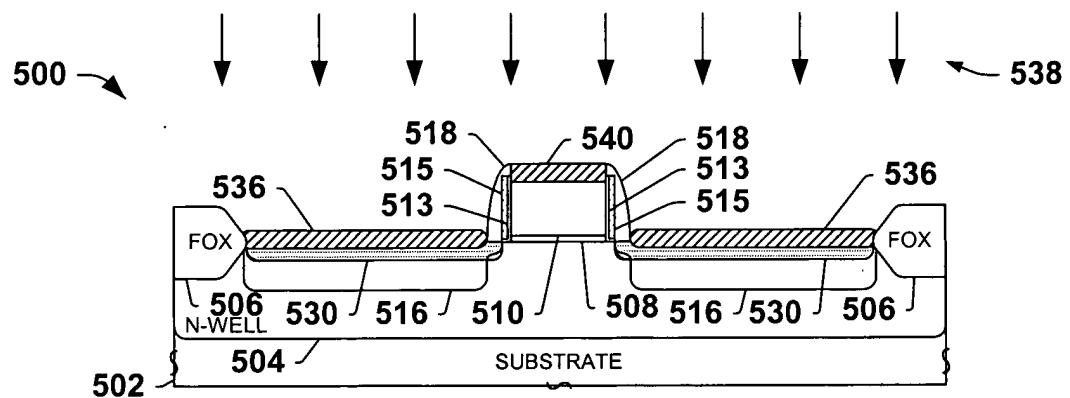


FIG. 7I